

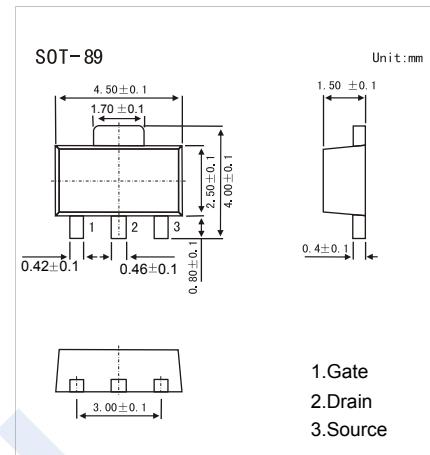
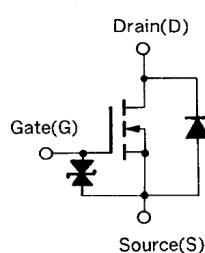
N-Channel MOSFET

2SK1587-HF

■ Features

- $V_{DS}(V) = 16V$
- $I_D = 2 A$
- $R_{DS(ON)} < 0.5 \Omega$ ($V_{GS} = 4V$)
- $R_{DS(ON)} < 0.8 \Omega$ ($V_{GS} = 2.5V$)
- Pb-Free Package May be Available.

The G-Suffix Denotes a Pb-Free Lead Finish

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	16	V
Gate-Source Voltage	V_{GS}	± 16	
Continuous Drain Current	I_D	2	A
Pulsed Drain Current (Note.1)	I_{DM}	4	
Power Dissipation	P_D	2	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to 150	

Note.1: $P_W \leq 10\text{ms}$, Duty Cycle $\leq 50\%$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D=250 \mu A$, $V_{GS}=0V$	16			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=16V$, $V_{GS}=0V$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS}=0V$, $V_{GS}=\pm 16V$			± 5	μA
Gate Cut-off Voltage	$V_{GS(off)}$	$V_{DS}=10V$, $I_D=1mA$	0.8		1.6	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=4V$, $I_D=1A$			0.5	Ω
		$V_{GS}=2.5V$, $I_D=0.5A$			0.8	
Forward Transconductance	g_{FS}	$V_{DS}=5V$, $I_D=1A$	0.4			S
Input Capacitance	C_{iss}	$V_{GS}=0V$, $V_{DS}=5V$, $f=1\text{MHz}$		180		pF
Output Capacitance	C_{oss}			160		
Reverse Transfer Capacitance	C_{rss}			55		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS(on)}=3V$, $V_{DS}=10V$, $I_D=1A$, $R_L=10\Omega$, $R_G=10\Omega$		100		ns
Turn-On Rise Time	t_r			700		
Turn-Off Delay Time	$t_{d(off)}$			150		
Turn-Off Fall Time	t_f			200		

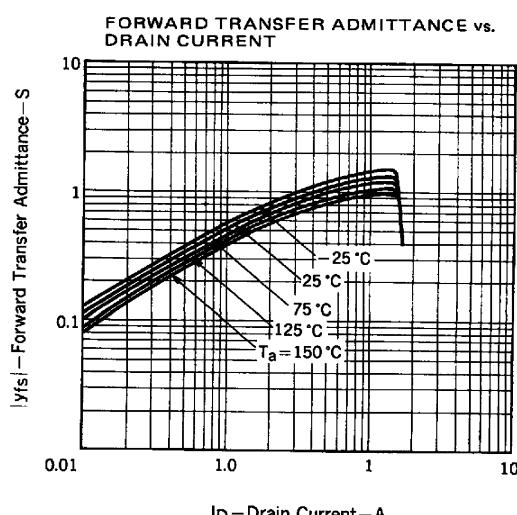
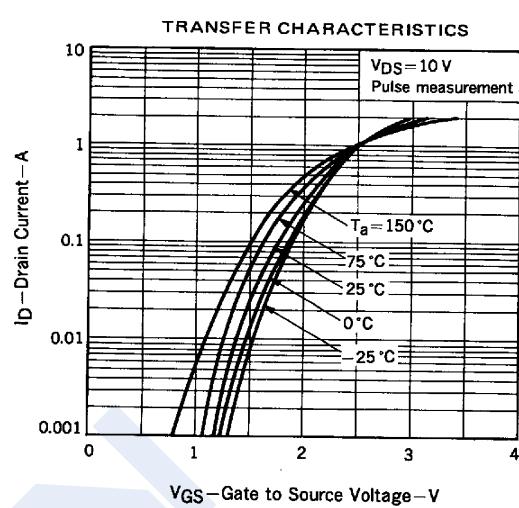
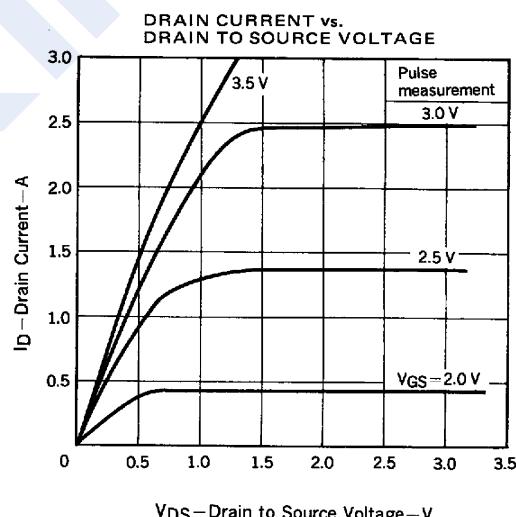
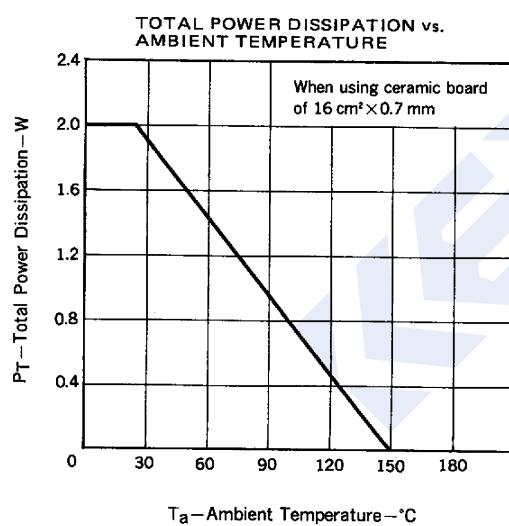
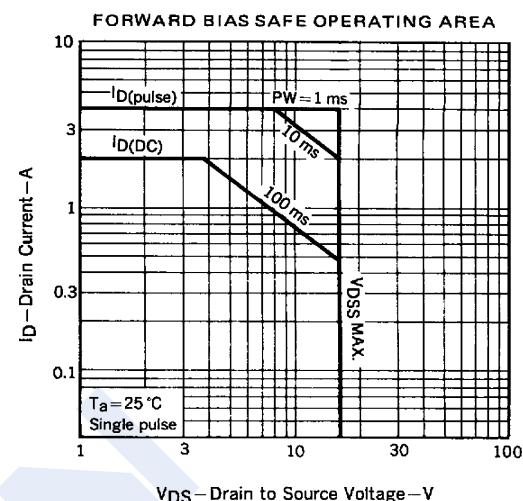
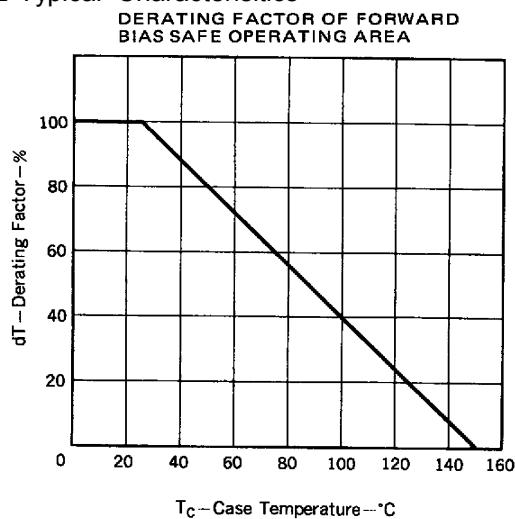
■ Marking

Marking	NF_F
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■ Typical Characteristics



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